SiA485DJ

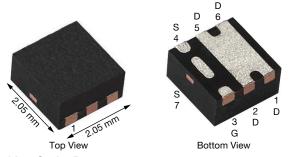
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Vishay Siliconix

P-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A)	Q _g (Typ.)		
-150	2.6 at V _{GS} = -10 V	-1.6 ^a	4.2 nC		
	2.7 at V _{GS} = -6 V	-1.6 ^a	4.2 110		

PowerPAK[®] SC-70-6L Single



TrenchFET[®] power MOSFET

FEATURES

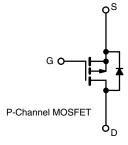
Thermally enhanced PowerPAK[®] SC-70 package
Small footprint area
Low on-resistance

• 100 % R_g and UIS tested

 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Active clamp switch
- Load switch



Marking Code: B4

Ordering Information:

SiA485DJ-T1-GE3 (Lead (Pb)-free and halogen-free)

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless	otherwise noted)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V _{DS}	-150	V		
Gate-Source Voltage	V _{GS}	± 20	v		
	T _C = 25 °C		-1.6		
Continuous Duoin Current (T. 150 °C)	T _C = 70 °C		-1.3		
Continuous Drain Current ($T_J = 150 \ ^\circ C$)	T _A = 25 °C	I _D	-0.7 ^{b, c}		
	T _A = 70 °C		-0.57 ^{b, c}	A	
Pulsed Drain Current (t = 100 µs)		I _{DM}	-2	A	
Continuous Course Ducia Dia da Cumant	T _C = 25 °C		-1.6		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	-1.6 ^{b, c}		
Avalanche Current		I _{AS}	-1.5		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	0.1	mJ	
Maximum Power Dissipation	T _C = 25 °C		15.6		
	T _C = 70 °C		10	w	
	T _A = 25 °C	P _D	2.9 ^{b, c}	VV	
	T _A = 70 °C		1.8 ^{b, c}		
Operating Junction and Storage Temperature R	T _J , T _{stg}	-55 to +150	*0		
Soldering Recommendations (Peak Temperatur		260			

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	32	43	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	6	8	0/10	

Notes

a. $T_C = 25 \ ^{\circ}C.$

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 80 °C/W.

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COMPLIANT

HALOGEN

FREE



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0, I_D = -250 \ \mu A$	-150 -		-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$	-2.5	-	-4.5	V	
Gate-Source Leakage	I _{GSS}	I_{GSS} $V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
Zara Cata Valtaga Duria Comunit	I _{DSS}	$V_{DS} = -150 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$ -		-	-1		
Zero Gate Voltage Drain Current		V_{DS} = -150 V, V_{GS} = 0 V, T_{J} = 55 $^{\circ}\text{C}$	-	-	-10	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, \text{ V}_{GS} = -10 \text{ V}$	-0.8	-	-	Α	
Drain-Source On-State Resistance ^a	D	V_{GS} = -10 V, I _D = -0.5 A	-	2.1	2.6	Ω	
	R _{DS(on)}	$V_{GS} = -6 \text{ V}, \text{ I}_{D} = -0.5 \text{ A}$	-	2.2	2.7		
Forward Transconductance ^a	g _{fs}	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -0.5 \text{ A}$	-	1.5	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}		-	155	-	pF	
Output Capacitance	C _{oss}	V_{DS} = -75 V, V_{GS} = 0 V, f = 1 MHz	-	8	-		
Reverse Transfer Capacitance	C _{rss}		-	5.5	-		
Total Gate Charge	Qg		-	4.2	6.3	nC	
Gate-Source Charge	Q _{gs}	V_{DS} = -75 V, V_{GS} = -10 V, I_{D} = -0.5 A	-	0.9	-		
Gate-Drain Charge	Q _{gd}		-	1.3	-		
Gate Resistance	Rg	f = 1 MHz	2	10	20	Ω	
Turn-On Delay Time	t _{d(on)}		-	5	10	- ns	
Rise Time	t _r	V_{DD} = -75 V, R_L = 75 Ω	-	20	40		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong-1~A,V_GEN=-10~V,R_g=1~\Omega$	-	10	20		
Fall Time	t _f		-	20	40		
Drain-Source Body Diode Characterist	cs						
Continuous Source-Drain Diode Current	I _S	$T_{C} = 25 \ ^{\circ}C$	-		-1.6	٨	
Pulse Diode Forward Current	I _{SM}		-		-2	A	
Body Diode Voltage	V _{SD}	$I_{\rm S}$ = -0.5 A, $V_{\rm GS}$ = 0 V	-	-0.8	-1.2	V	
Body Diode Reverse Recovery Time	t _{rr}		-	40	80	ns	
Body Diode Reverse Recovery Charge	Q _{rr}		-	65	130	nC	
Reverse Recovery Fall Time	t _a	I _F = -1 A, dl/dt = 100 A/μs, T _J = 25 °C	-	28	-		
verse Recovery Rise Time t _b		-	12	-	ns		

Notes

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

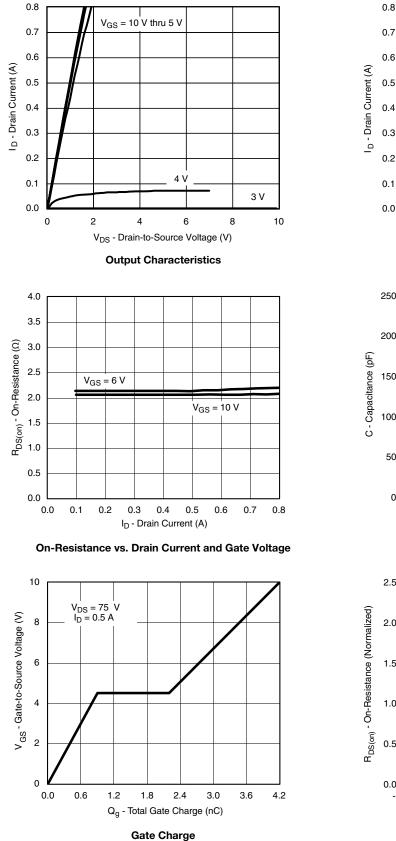
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

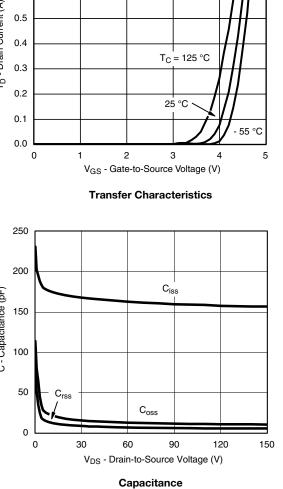
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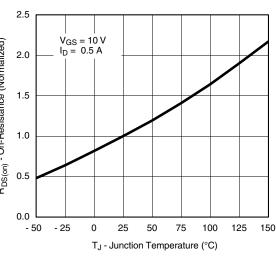
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)







On-Resistance vs. Junction Temperature

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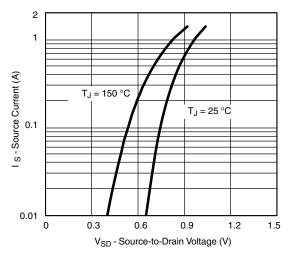
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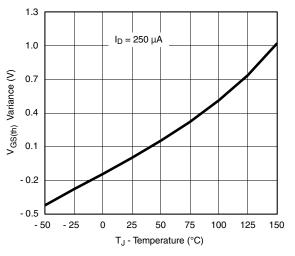
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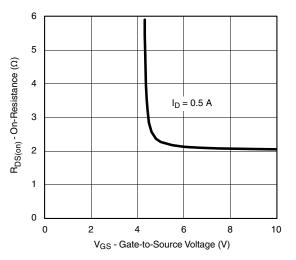
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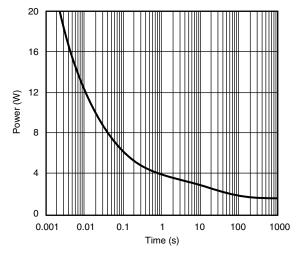
Source-Drain Diode Forward Voltage



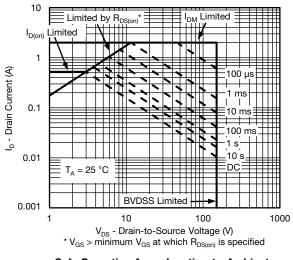
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient 4

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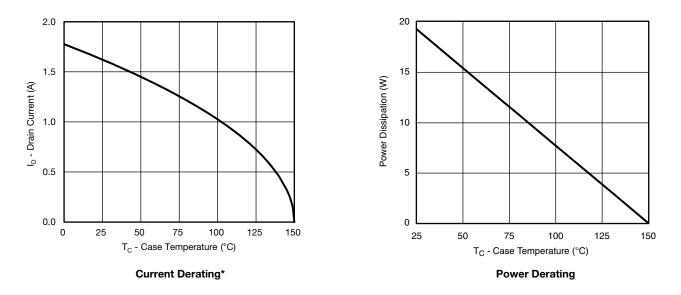
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

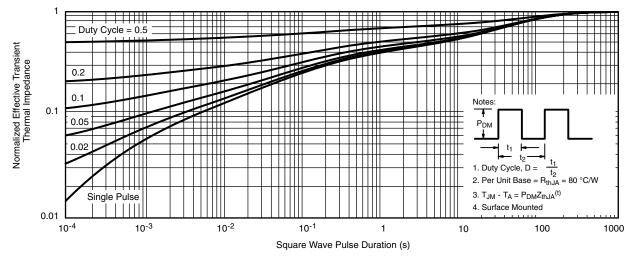


* The power dissipation P_D is based on $T_{J (max.)} = 150 \text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

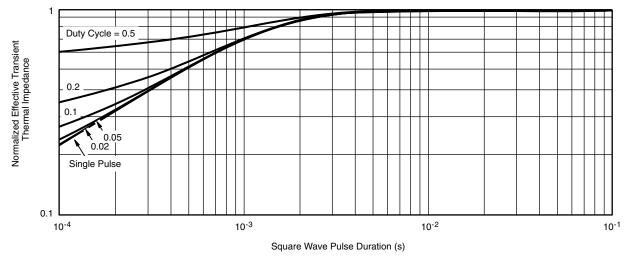


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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62988.



PowerPAK[®] SC70-6L

VISHA

b PIN2 PIN1 PIN3 _ ₹



b

PIN3

__ ₿

PIN2

PIN1

¥

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¹



RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC70-6L Single



Dimensions in mm/(Inches)

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